

Ratings and characteristics of FUJI IGBT

1. 1MBH50-090 (MBT002)

2. Absolute maximum ratings ($T_c=25^{\circ}\text{C}$)

Items	Symbols	Ratings	Conditions	Unit
Collector-Emitter Voltage	V_{CES}	900		V
Gate-Emitter Voltage	V_{GES}	± 20		V
Collector-Current	I_C	50		A
	I_{CP}	150	$50\mu\text{s}$	A
Max.Power dissipation	PC	200		W
Operating temperature	T_j	+150		$^{\circ}\text{C}$
Storage temperature	T_{stg}	-40~+150		$^{\circ}\text{C}$

3. Electrical characteristics ($T_c=25^{\circ}\text{C}$)

Items	Symbols	Conditions	MIN.	TYP.	MAX.	Unit
Collector-cutoff current	I_{CES}	$V_{CE}=800\text{V}, V_{GE}=0\text{V}$			100	μA
Gate-leakge current	I_{GES}	$V_{GE}=20\text{V}, V_{CE}=0\text{V}$			100	nA
Collector-Emitter Voltage	V_{CE}	$I_C = 1\text{mA}, V_{GE}=0\text{V}$	900			V
Threshold Voltage	$V_{GE(th)}$	$I_C = 10\text{mA}, V_{CE}=10\text{V}$	2.0		6.0	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 50\text{A}, V_{GE}=15\text{V}$			3.6	V
Input capacitance	C_{ies}	$V_{CE}=25\text{V}, V_{GE}=0\text{V}$		2400		pF
Switching characteristics	t_f	$I_C = 50\text{A}, V_{GE}=+15\text{V}$ see fig.2			0.85	μs
Thermal resistance	R_{thj-c}	junction-case			0.625	$^{\circ}\text{C/W}$

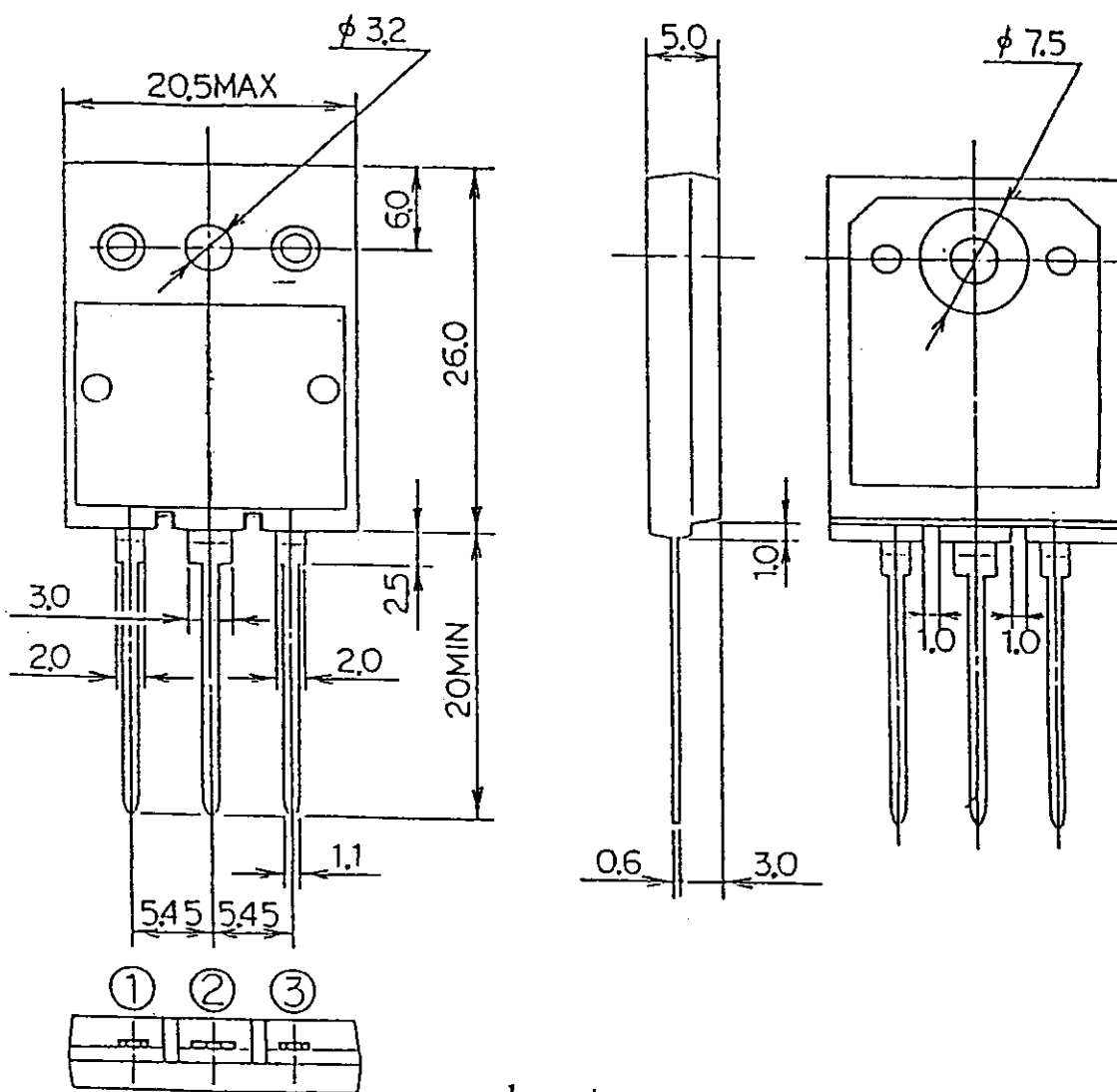
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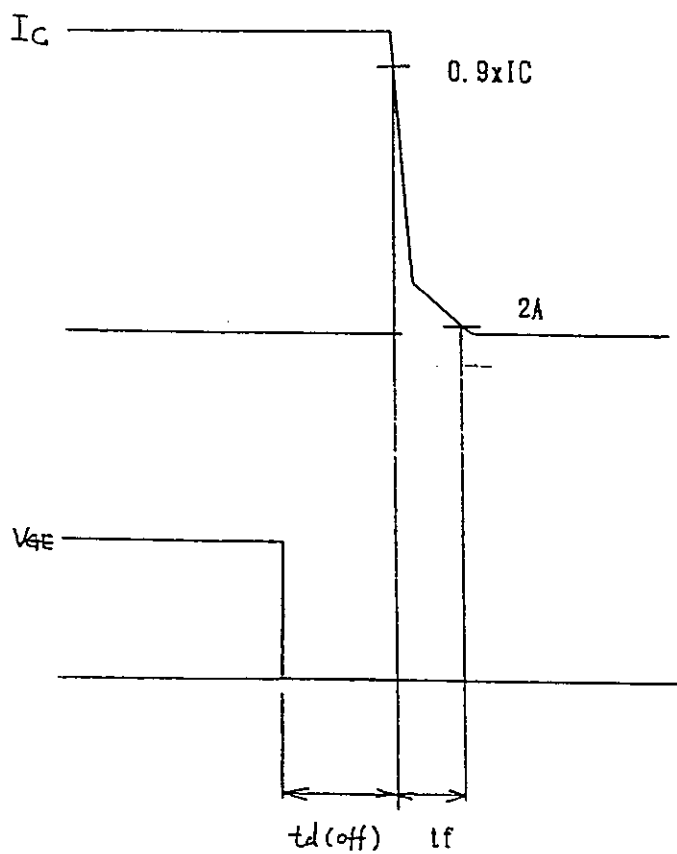
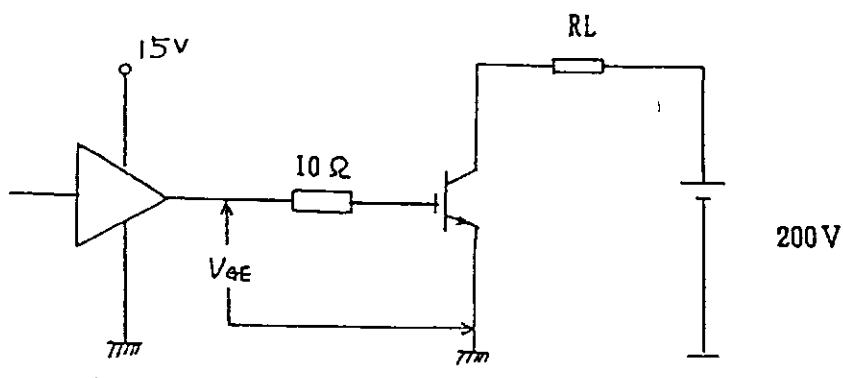
4. Out line



- 1 gate
- 2 Collector
- 3 Emitter

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Fig.2 Test circuit of switching characteristics



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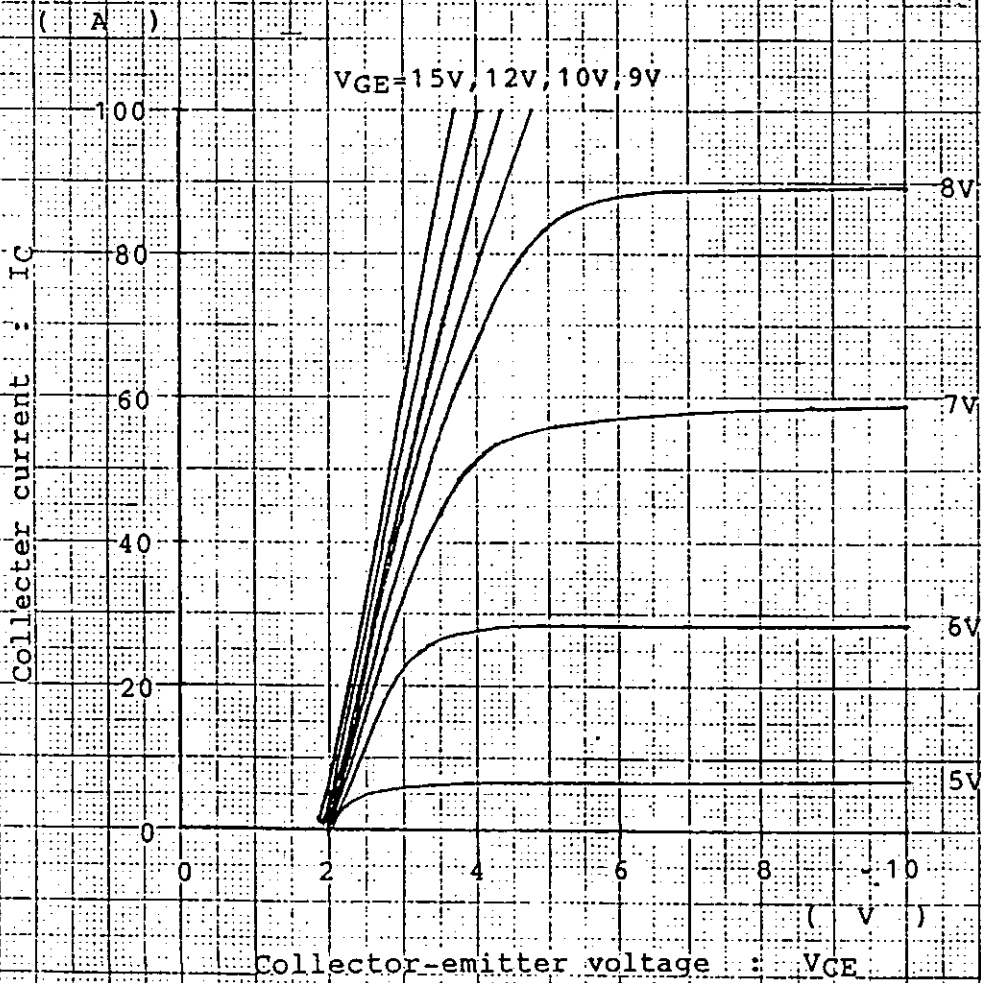
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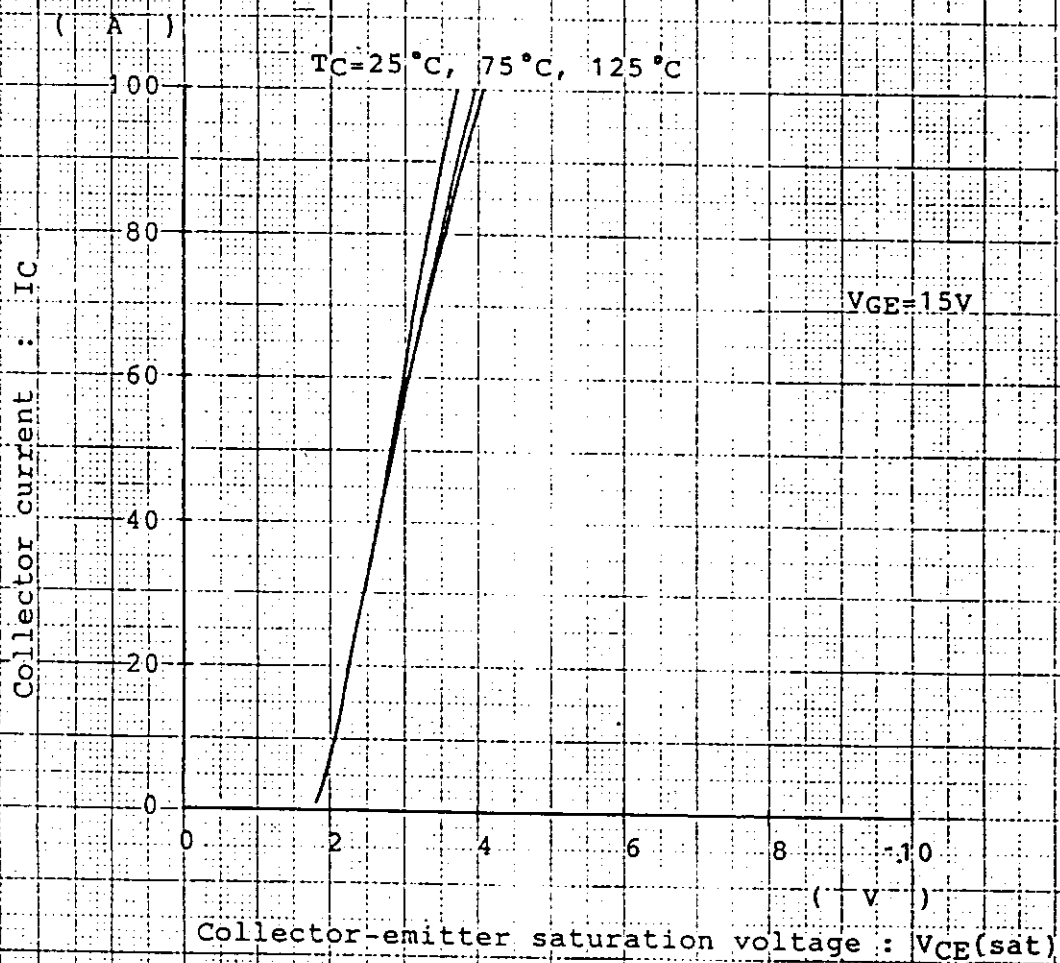
Typical output characteristics

$T_C = 25^\circ\text{C}$



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Collector current vs.
Collector-emitter saturation voltage



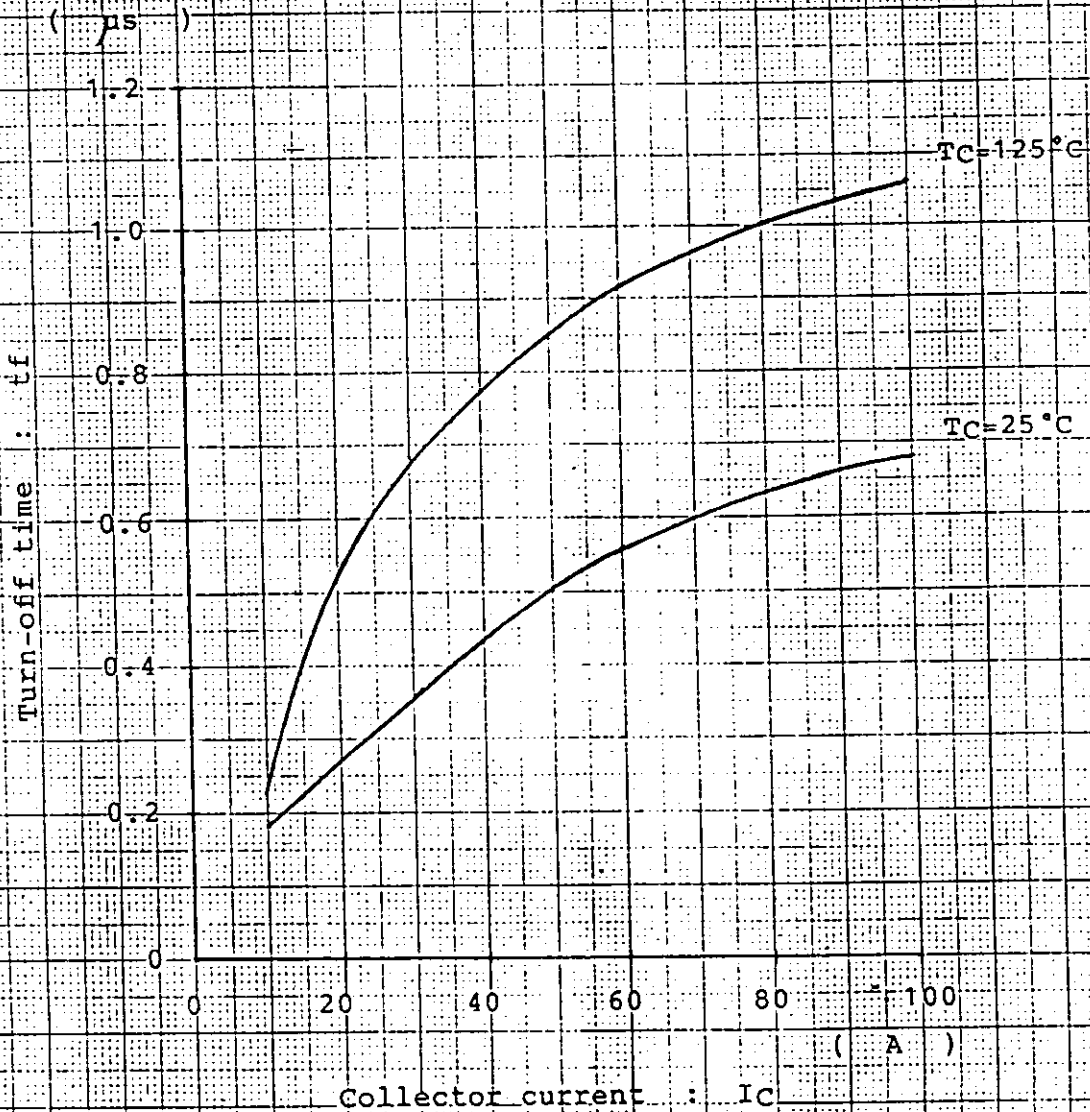
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Typical t_f vs. Collector current

$V_{GE}=15V$



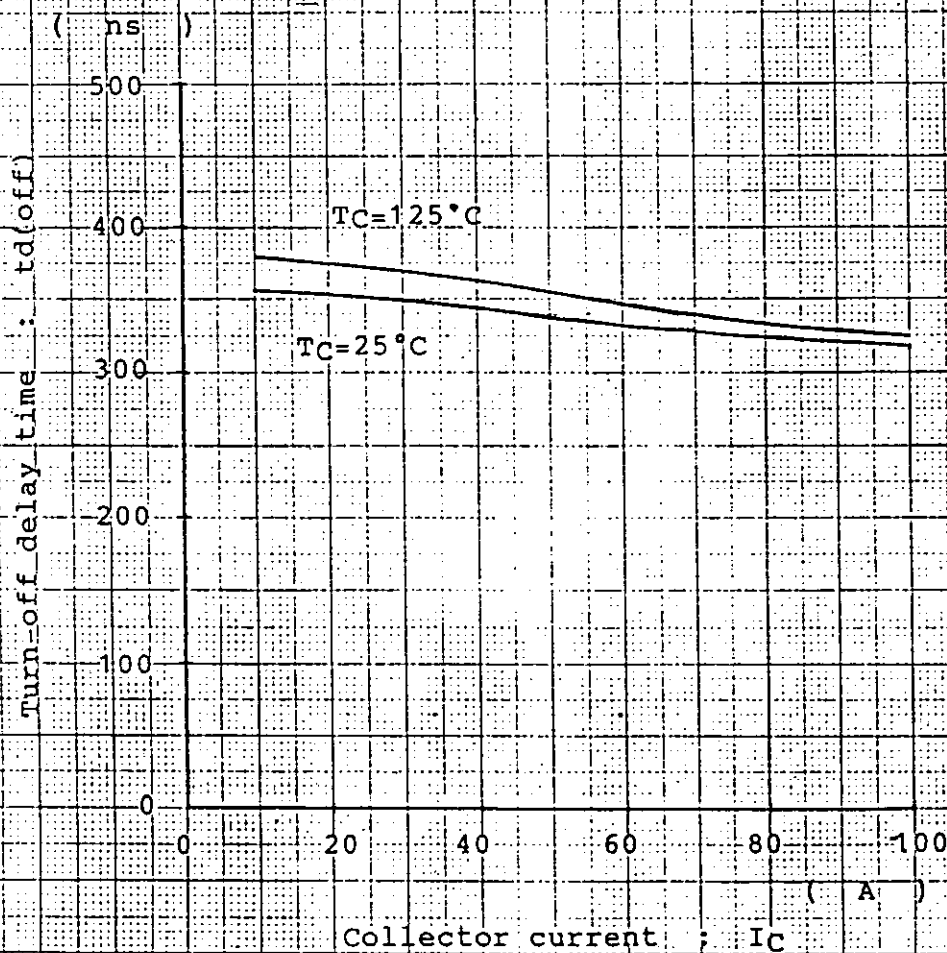
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Typical Turn-off delaytime
vs. Collector current

$V_{GE}=15V$



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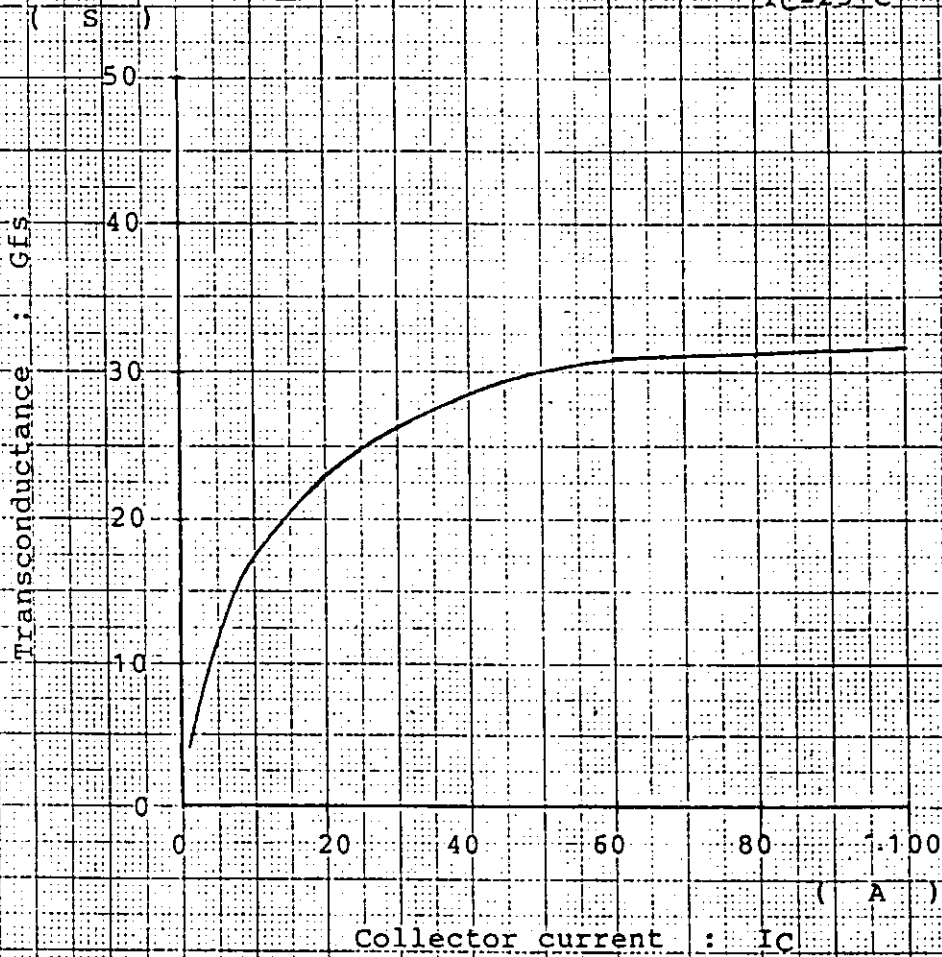
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Typical transconductance

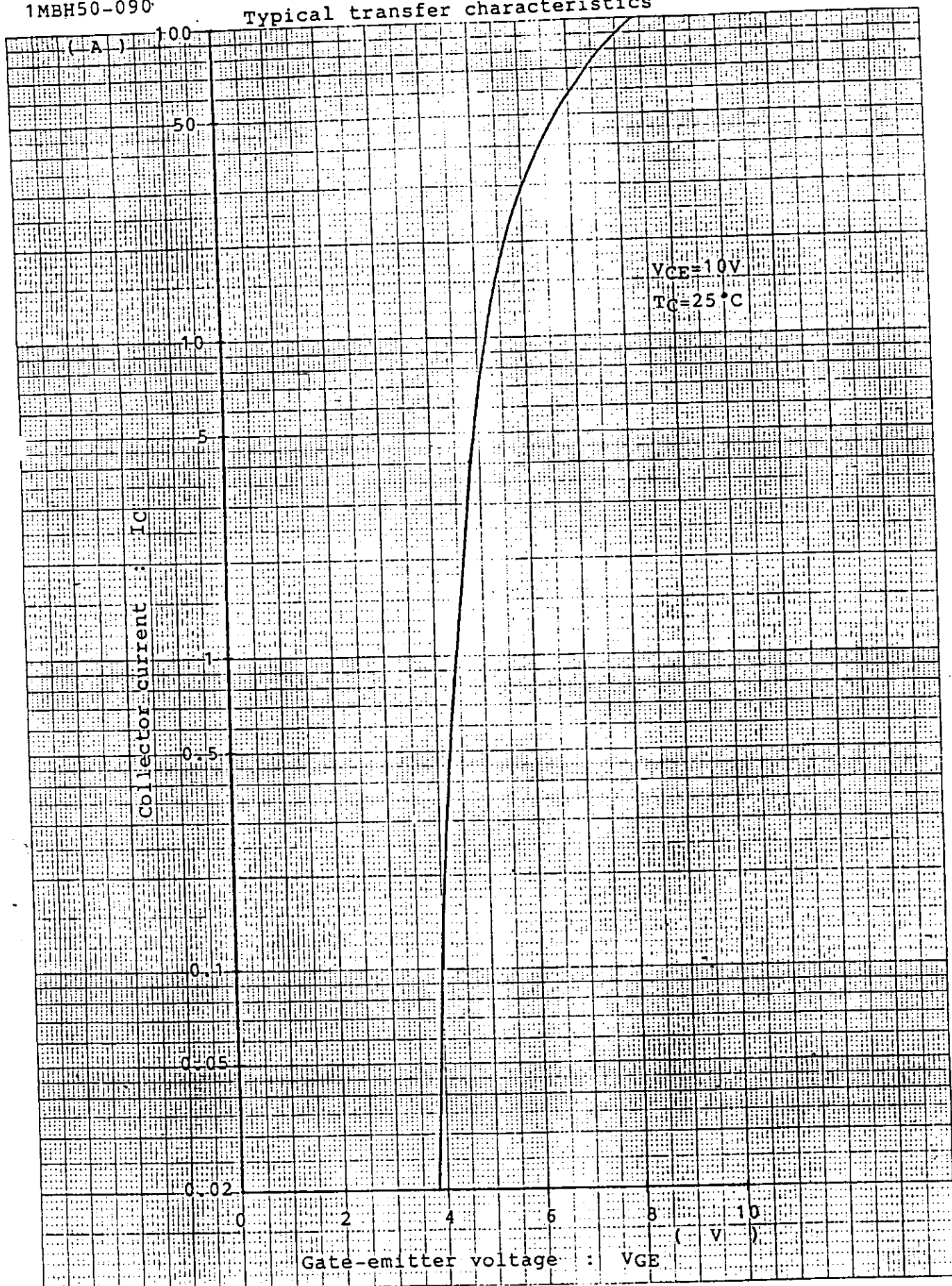
$V_{CE}=10V$

$T_C=25^{\circ}C$



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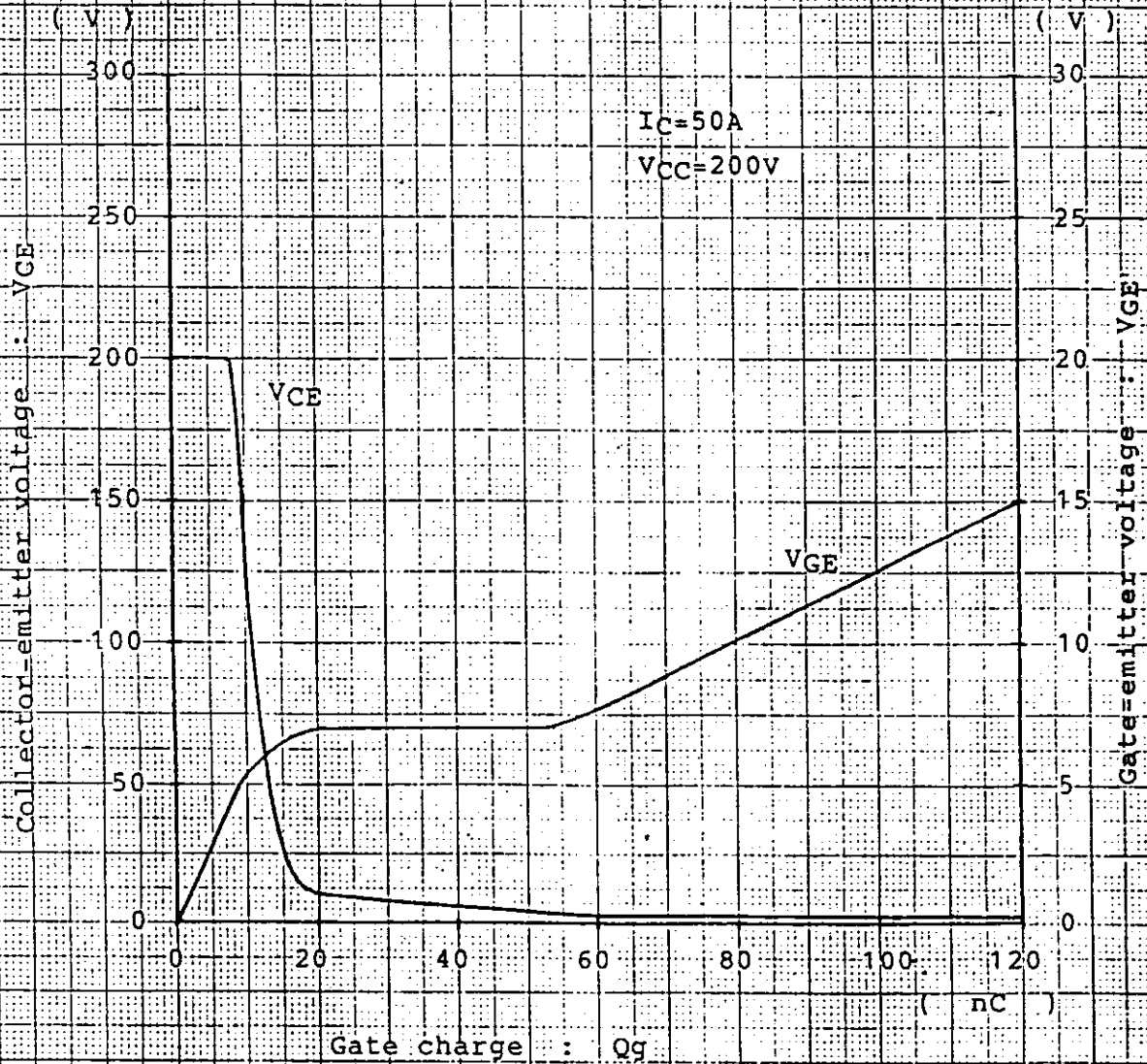
Typical transfer characteristics



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Dynamic input characteristics



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Typical threshold voltage
vs. Junction temperature

$V_{CE}=10V$
 $I_C=10mA$

Gate-emitter threshold voltage : $V_{GE(th)}$ (V)

5

4

3

2

1

0

0

20

40

60

80

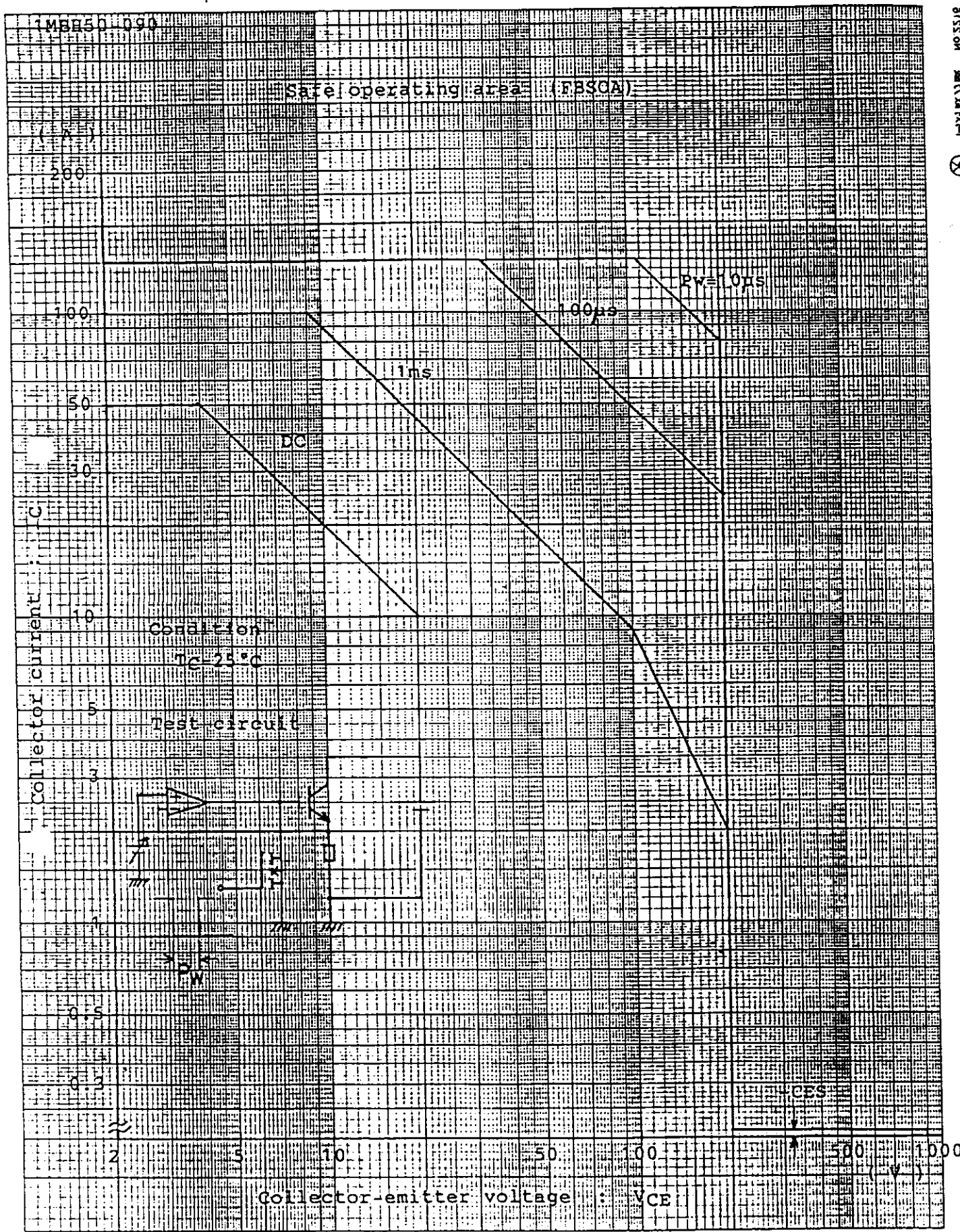
100

120

140

(°C)

Junction temperature : T_j



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